

FAST - 110713689.wsp

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 L16: (0) memory adj cell and (bit near line\$1 near demarc\$2)
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 L18: (909) memory adj cell and ((bit near line\$1)) and trench\$2 and gate near dielectric
 L19: (102) 18 and diffusion near barrier
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 Default operator: ☒ Highlight all hit terms initially
 18 and diffusion near barrier

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| 79 | <input type="checkbox"/> | <input type="checkbox"/> | US 6492222 B1 | 20021210 | 19 | Method of dry etching PZT capacitor stack to form high-density ferroelectric memory | 438/240 | 438/239; 438/250; |
| 80 | <input type="checkbox"/> | <input type="checkbox"/> | US 6485988 B2 | 20021126 | 21 | Hydrogen-free contact etch for ferroelectric capacitor formation | 438/3 | 257/E21.009; 257/E21.011; |
| 81 | <input type="checkbox"/> | <input type="checkbox"/> | US 6475855 B1 | 20021105 | 22 | Method of forming integrated circuitry, method of forming a capacitor and method | 438/239 | 438/250; 438/251; |
| 82 | <input type="checkbox"/> | <input type="checkbox"/> | US 6465828 B2 | 20021015 | 37 | Semiconductor container structure with diffusion barrier | 257/296 | 257/301; 257/303; |
| 83 | <input type="checkbox"/> | <input type="checkbox"/> | US 6440801 B1 | 20020827 | 73 | Structure for folded architecture pillar memory cell | 438/272 | 257/302; 257/330; |
| 84 | <input type="checkbox"/> | <input type="checkbox"/> | US 6420272 B1 | 20020716 | 9 | Method for removal of hard mask used to define noble metal electrode | 438/702 | 216/16; 216/39; |
| 85 | <input type="checkbox"/> | <input type="checkbox"/> | US 6366489 B1 | 20020402 | 26 | Bi-state ferroelectric memory devices, uses and operation | 365/145 | 365/149 |
| 86 | <input type="checkbox"/> | <input type="checkbox"/> | US 6348709 B1 | 20020219 | 18 | Electrical contact for high dielectric constant capacitors and method for fabricating the | 257/311 | 257/310; 257/751; |
| 87 | <input type="checkbox"/> | <input type="checkbox"/> | US 6348705 B1 | 20020219 | 28 | Low temperature process for high density thin film integrated capacitors and | 257/295 | 257/310; 257/E21.272; |
| 88 | <input type="checkbox"/> | <input type="checkbox"/> | US 6335238 B1 | 20020101 | 9 | Integrated dielectric and method | 438/240 | 257/77; 257/E21.009; |
| 89 | <input type="checkbox"/> | <input type="checkbox"/> | US 6259126 B1 | 20010710 | 23 | Low cost mixed memory integration with FERAM | 257/298 | 257/303; 257/315; |

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